

R2

PATENT ABSTRACTS OF JAPAN

(11)Publication number : 62-077491

(43)Date of publication of application : 09.04.1987

(51)Int.Cl.

C25D 1/04
C22C 1/00
C22C 33/00

(21)Application number : 60-217288

(71)Applicant : SUMITOMO METAL IND LTD

(22)Date of filing : 30.09.1985

(72)Inventor : KONDO KAZUO

(54) PRODUCTION OF HIGH RESISTANCE AMORPHOUS NiP FOIL STRIP OF LARGE WIDTH

(57)Abstract:

PURPOSE: To produce high resistance amorphous NiP foil of a large width by pulse electrolysis by depositing an NiP alloy on a substrate at a specified current density with a specified period of pulsation in a bath prep'd. by mixing a Watts bath with an oxy-acid of phosphorus or a salt thereof and by stripping the resulting NiP alloy film. CONSTITUTION: A bath prep'd. by mixing a Watts bath with an oxy-acid of phosphorus or a salt thereof such as phosphorous acid, hypophosphorous acid or sodium hypophosphite is used. A pulsating current ip having 0.01W100msec on-time and off-time is supplied at a current density represented by the formula to deposit an NiP alloy on a substrate of an easily passivatable and electrically conductive material. The resulting NiP alloy film is stripped from the substrate. Thus, high resistance amorphous NiP foil of large width is obtd.

1 2 3 4 5 6 7 8 9 10 11 12 13 14 15 16 17 18 19 20 21 22 23 24 25 26 27 28 29 30 31 32 33 34 35 36 37 38 39 40 41 42 43 44 45 46 47 48 49 50 51 52 53 54 55 56 57 58 59 60 61 62 63 64 65 66 67 68 69 70 71 72 73 74 75 76 77 78 79 80 81 82 83 84 85 86 87 88 89 90 91 92 93 94 95 96 97 98 99 100